The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A method of supporting a flexible substrate, comprising the step of:

fixing the flexible substrate having thermal shrinkage to a holding frame having a smaller thermal expansion coefficient than 10 ppm/°C.

2. (Original) A method of supporting a flexible substrate, comprising the step of:

fixing an outer circumference of the flexible substrate having thermal shrinkage to a frame-shaped holding frame having a smaller thermal expansion coefficient than 10 ppm/°C.

3. (Original) A method of supporting a flexible substrate according to claim 1, wherein the flexible substrate comprises one selected from polyethylene naphthalate, polyethylene terephthalate, polyether sulfone, and polyimide.

4. (Previously presented) A method of supporting a flexible substrate according to claim 1, wherein the holding frame comprises a ceramics-metal complex.

5. (Original) A method of supporting a flexible substrate according to claim 2, wherein the flexible substrate comprise one selected from polyethylene naphthalate, polyethylene terephthalate, polyether sulfone, and polyimide.

6. (Previously presented) A method of supporting a flexible substrate according to claim 2, wherein the holding frame comprises a ceramics-metal complex.

7. (Original) A method of manufacturing a semiconductor device, comprising the step of:

fixing a flexible substrate having thermal shrinkage to a holding frame having a smaller thermal expansion coefficient than 10 ppm/°C; and

heating the flexible substrate at a temperature that the flexible substrate is thermal-shrunk by 0.2% or more.

8. (Original) A method of manufacturing a semiconductor device, comprising the step of:

fixing an outer circumference of a flexible substrate having thermal shrinkage to a frame-shaped holding frame having a smaller thermal expansion coefficient than 10 ppm/°C and; and

heating the flexible substrate at a temperature that the flexible substrate is thermal-shrunk by 0.2% or more.

9. (Original) A method of manufacturing a semiconductor device, comprising the step of:

fixing an outer circumference of a flexible substrate having thermal shrinkage to a frame-shaped holding frame having a smaller thermal expansion coefficient than 10 ppm/°C;

heating the fixed flexible substrate at a temperature that the flexible substrate is thermal-shrunk by 0.2% or more; and

forming a conductive film on the flexible substrate by a sputtering method.

10. (Original) A method of manufacturing a semiconductor device, comprising the step of:

fixing an outer circumference of a flexible substrate having thermal shrinkage to a frame-shaped holding frame having a smaller thermal expansion coefficient than 10 ppm/°C;

heating the fixed flexible substrate at a temperature that the flexible substrate is thermal-shrunk by 0.2% or more; and

forming an amorphous semiconductor film on the flexible substrate by a plasma CVD method.

11. (Original) A method of manufacturing a semiconductor device, comprising:

a first step of fixing an outer circumference of a flexible substrate having thermal shrinkage to a frame-shaped holding frame having a smaller thermal expansion coefficient than 10 ppm/°C and then heating the flexible substrate at a temperature that the flexible substrate is thermal-shrunk by 0.2% or more; and

a second step of forming a predetermined pattern over the flexible substrate by screen printing.

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12. (Original) A method of manufacturing a semiconductor device, comprising:

a first step of fixing an outer circumference of a flexible substrate having thermal shrinkage to a frame-shaped holding frame having a smaller thermal expansion coefficient than 10 ppm/°C and then heating the flexible substrate at a temperature that the flexible substrate is thermal-shrunk by 0.2% or more; and

a second step of forming a predetermined pattern over the flexible substrate by laser processing.

13. (Currently amended) A method of manufacturing a semiconductor device according to claim 11, wherein a position of the flexible substrate is aligned by an ~~alignemt~~ alignment means of the holding frame in the second step.

14. (Currently amended) A method of manufacturing a semiconductor device according to claim 12, wherein a position of the flexible substrate is aligned by an ~~alignemt~~ alignment means of the holding frame in the second step.

15. (Currently amended) A method of manufacturing a semiconductor device according to claim 7, wherein the flexible substrate comprises one selected from polyethylene naphthalate, polyethylene terephthalate, polyether ~~sulfon~~ sulfone, and polyimide.

16. (Previously presented) A method of supporting a flexible substrate according to claim 7, wherein the holding frame comprises a ceramics-metal complex.

17. (Currently amended) A method of manufacturing a semiconductor device according to claim 8, wherein the flexible substrate comprises one selected from polyethylene naphthalate, polyethylene terephthalate, polyether ~~sulfon~~ sulfone, and polyimide.

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18. (Previously presented) A method of supporting a flexible substrate according to claim 8, wherein the holding frame comprises a ceramics-metal complex.

19. (Currently amended) A method of manufacturing a semiconductor device according to claim 9, wherein the flexible substrate comprises one selected from polyethylene naphthalate, polyethylene terephthalate, polyether ~~sulfon~~ sulfone, and polyimide.

20. (Previously presented) A method of supporting a flexible substrate according to claim 9, wherein the holding frame comprises a ceramics-metal complex.

21. (Currently amended) A method of manufacturing a semiconductor device according to claim 10, wherein the flexible substrate comprises one selected from polyethylene naphthalate, polyethylene terephthalate, polyether ~~sulfon~~ sulfone, and polyimide.

22. (Previously presented) A method of supporting a flexible substrate according to claim 10, wherein the holding frame comprises a ceramics-metal complex.

23. (Currently amended) A method of manufacturing a semiconductor device according to claim 11, wherein the flexible substrate comprises one selected from polyethylene naphthalate, polyethylene terephthalate, polyether ~~sulfon~~ sulfone, and polyimide.

24. (Previously presented) A method of supporting a flexible substrate according to claim 11, wherein the holding frame comprises a ceramics-metal complex.

25. (Original) A method of manufacturing a semiconductor device according to claim 12, wherein the flexible substrate comprises one selected from polyethylene naphthalate, polyethylene terephthalate, polyether sulfone, and polyimide.

26. (Previously presented) A method of supporting a flexible substrate according to claim 12, wherein the holding frame comprises a ceramics-metal complex.

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27. (Previously presented) A method of supporting a flexible substrate according to claim 1, wherein the thermal expansion coefficient is 6.5 ppm/°C or smaller.

28. (Previously presented) A method of supporting a flexible substrate according to claim 2, wherein the thermal expansion coefficient is 6.5 ppm/°C or smaller.

29. (Previously presented) A method of supporting a flexible substrate according to claim 7, wherein the thermal expansion coefficient is 6.5 ppm/°C or smaller.

30. (Previously presented) A method of supporting a flexible substrate according to claim 8, wherein the thermal expansion coefficient is 6.5 ppm/°C or smaller.

31. (Previously presented) A method of supporting a flexible substrate according to claim 9, wherein the thermal expansion coefficient is 6.5 ppm/°C or smaller.

32. (Previously presented) A method of supporting a flexible substrate according to claim 10, wherein the thermal expansion coefficient is 6.5 ppm/°C or smaller.

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33. (Previously presented) A method of supporting a flexible substrate according to claim 11, wherein the thermal expansion coefficient is 6.5 ppm/°C or smaller.

34. (Previously presented) A method of supporting a flexible substrate according to claim 12, wherein the thermal expansion coefficient is 6.5 ppm/°C or smaller.